

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	285	L5 and @pd>"20070101"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 16:08
S8	441	S7 and @pd>"20060803"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 16:07
L5	6966	257/66,72,347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 16:07
L4	121	3 and @py<"1992"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 13:56
L3	17897	2 and (pixel near2 electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 13:56
L2	32724	1 and (gate with substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 13:55
L1	127073	(thin adj film adj transistor) or TFT	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/12 13:55

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S37	50	((ALN or (aluminum near nitride)) with (layer or film)) with ((carbon)) with (stress or strain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:22
S36	1323	S35 and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:22
S35	1528	((ALN or (aluminum near nitride)) with (layer or film)) with ((carbon))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:22
S34	1660	((ALN or (aluminum near nitride)) with (layer or film)) with ((carbon or (C with O)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:22
S32	256	S31 and substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:22
S33	3510	((ALN or (aluminum near nitride)) with (layer or film)) with ((carbon or C))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:21
S31	270	((ALN or (aluminum near nitride)) with (layer or film)) same ((carbon or C) with (doped or dopant or cotaminat\$6))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:21

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S30	59	(ALN or (aluminum near nitride)) with (carbon with (stress or strain))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:11
S29	0	(ALN or (aluminum near nitride)) with (barrier or passivat\$5) with (carbon with (stress or strain))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:05
S28	397	(ALN or (aluminum near nitride)) with (barrier or passivat\$5) with (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 18:02
S24	1800	(ALN or (aluminum near nitride)) with (barrier)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/05 15:31